



IR-1609 (2-1941)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Patent Application of

Daniel M. Kinzer

Date: November 17, 1999

Serial No. 09/292,186

Group Art Unit: 2811

Filed: April 15, 1999

Examiner:

For: P-CHANNEL TRENCH MOSFET STRUCTURE

Asst. Commissioner for Patents
Washington, D.C. 20231

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NOV 23 1999

PRELIMINARY AMENDMENT

TECHNOLOGY CENTER 2800

Sir:

Prior to examining the above-identified application, please amend the application as follows:

IN THE CLAIMS:

Please add new claims:

- At C3
could
- 9. A power MOSFET having reduced on resistance comprising, in combination; a P type conductivity substrate; an epitaxially deposited N type layer of the other conductivity type deposited atop said P type substrate and having a substantially constant concentration throughout its volume; a plurality of spaced trenches having vertical walls extending through said epitaxial layer; a thin gate oxide on said vertical walls and conductive polysilicon deposited into said trenches to define a polysilicon gate; a